## Thomas N Jackson

List of Publications by Year in descending order

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331670 552781 5,805 28 21 26 h-index citations g-index papers 30 30 30 6740 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Offset Drain ZnO Thin-Film Transistors for High-Voltage Operation. IEEE Electron Device Letters, 2017, 38, 1047-1050.	3.9	22
2	Flexibility Testing Strategies and Apparatus for Flexible Electronics. IEEE Transactions on Electron Devices, 2016, 63, 1934-1939.	3.0	29
3	Drain-offset ZnO thin film transistors for high voltage operations. , 2016, , .		O
4	Flexible high-temperature dielectric materials from polymer nanocomposites. Nature, 2015, 523, 576-579.	27.8	1,476
5	Controlling the Microstructure of Solution-Processable Small Molecules in Thin-Film Transistors through Substrate Chemistry. Chemistry of Materials, 2011, 23, 1194-1203.	6.7	67
6	Probing stress effects in single crystal organic transistors by scanning Kelvin probe microscopy. Applied Physics Letters, 2010, 96, .	3.3	18
7	ZnO pyroelectric thin film field-effect transistors. , 2009, , .		O
8	Effects of polymorphism on charge transport in organic semiconductors. Physical Review B, 2009, 80,	3.2	137
9	Thin-film morphology and transistor performance of alkyl-substituted triethylsilylethynyl anthradithiophenes. Journal of Materials Chemistry, 2009, 19, 7984.	6.7	36
10	Nonâ€Reliefâ€Pattern Lithography Patterning of Solution Processed Organic Semiconductors. Advanced Materials, 2008, 20, 4145-4147.	21.0	16
11	Surface Potential Imaging of Solution Processable Aceneâ€Based Thin Film Transistors. Advanced Materials, 2008, 20, 4513-4516.	21.0	46
12	Chromophore Fluorination Enhances Crystallization and Stability of Soluble Anthradithiophene Semiconductors. Journal of the American Chemical Society, 2008, 130, 2706-2707.	13.7	324
13	High-mobility spin-cast organic thin film transistors. Applied Physics Letters, 2008, 93, .	3.3	97
14	Organic Single-Crystal Field-Effect Transistors of a Soluble Anthradithiophene. Chemistry of Materials, 2008, 20, 6733-6737.	6.7	178
15	High-Speed, Low-Temperature Integrated ZnO/Organic CMOS Circuits. , 2008, , .		1
16	ZnO Thin-Film Transistor Ring Oscillators with 31-ns Propagation Delay. IEEE Electron Device Letters, 2008, 29, 721-723.	3.9	59
17	Correlation between microstructure, electronic properties and flicker noise in organic thin film transistors. Applied Physics Letters, 2008, 92, 132103.	3.3	82
18	Polymeric Substrate Spin-Cast diF-TESADT OTFT Circuits. IEEE Electron Device Letters, 2008, 29, 1004-1006.	3.9	32

#	Article	IF	CITATIONS
19	High mobility solution processed 6,13-bis(triisopropyl-silylethynyl) pentacene organic thin film transistors. Applied Physics Letters, 2007, 91, .	3.3	542
20	Effect of Light Illumination on Threshold Voltage and Sub-threshold Slope of Amorphous Silicon Thin Film Transistors. Materials Research Society Symposia Proceedings, 2006, 910, 3.	0.1	1
21	Organic Field-Effect Transistors from Solution-Deposited Functionalized Acenes with Mobilities as High as 1 cm2/V·s. Journal of the American Chemical Society, 2005, 127, 4986-4987.	13.7	735
22	Contact resistance in organic thin film transistors. Solid-State Electronics, 2003, 47, 297-301.	1.4	337
23	Template Synthesis of Metal Nanowires Containing Monolayer Molecular Junctions. Journal of the American Chemical Society, 2002, 124, 4020-4026.	13.7	198
24	Dielectric functions and optical bandgaps of high-K dielectrics for metal-oxide-semiconductor field-effect transistors by far ultraviolet spectroscopic ellipsometry. Journal of Applied Physics, 2002, 91, 4500-4505.	2.5	346
25	Optical characterization of 4H-SiC by far ultraviolet spectroscopic ellipsometry. Applied Physics Letters, 2001, 79, 162-164.	3.3	4
26	Electric-field assisted assembly and alignment of metallic nanowires. Applied Physics Letters, 2000, 77, 1399-1401.	3.3	876
27	A reduced complexity process for organic thin film transistors. Applied Physics Letters, 2000, 76, 1692-1694.	3.3	85
28	Fast, smooth, and anisotropic etching of SiC using SF[sub 6]/Ar. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2055.	1.6	17